

High Power Diode Hockey Puk Version R920 E...C Series

FEATURES

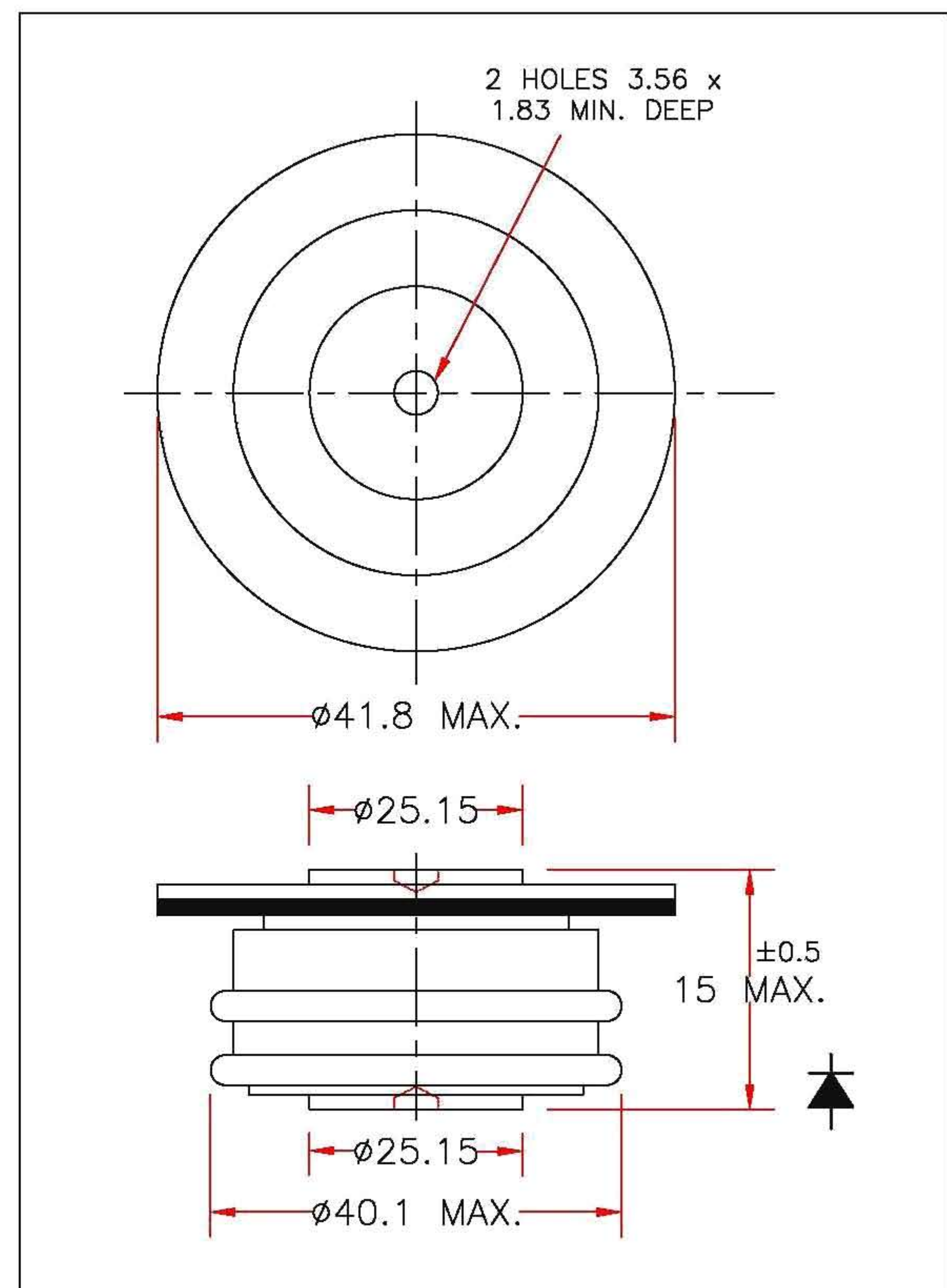
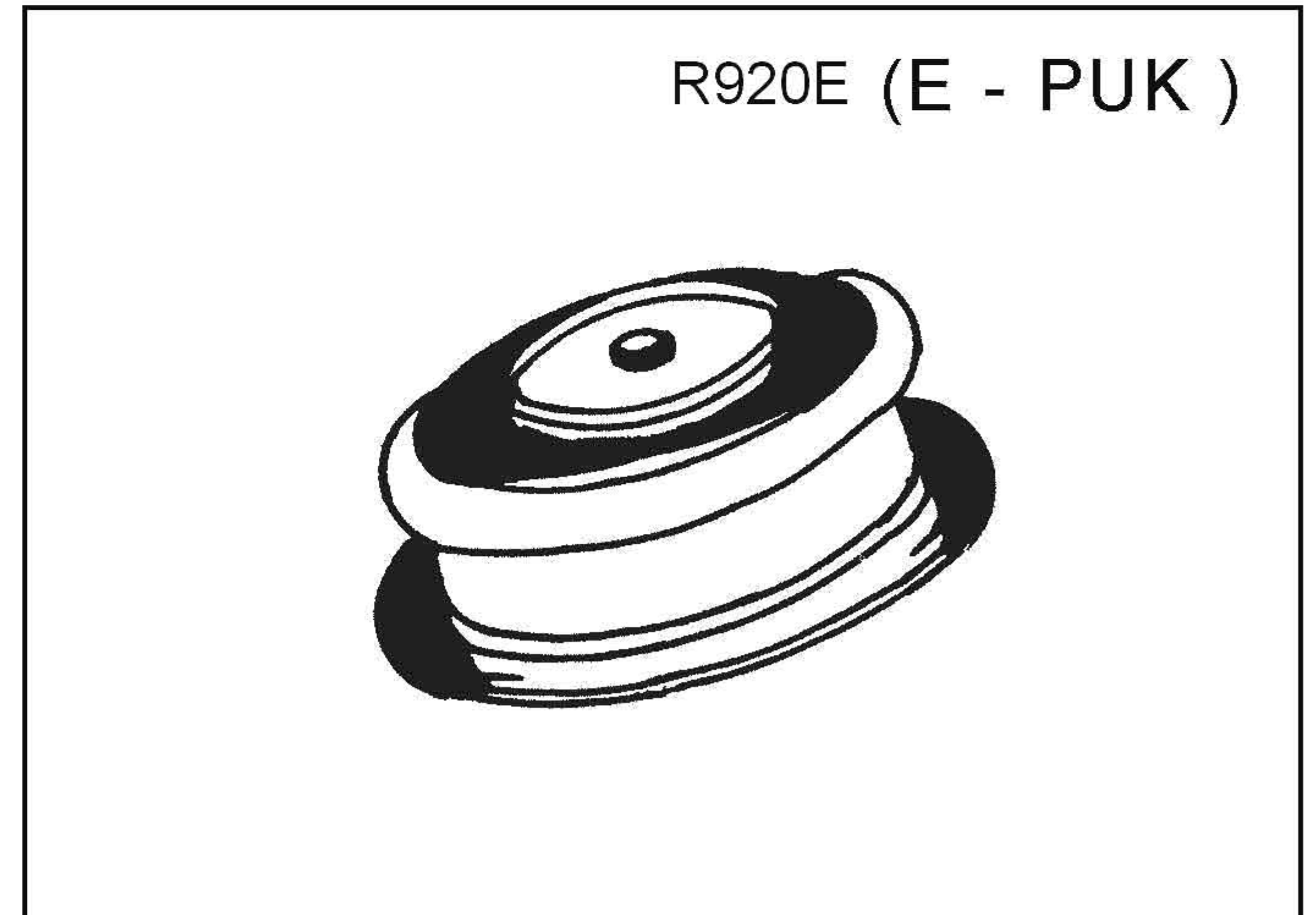
- ⌘ Wide current range
- ⌘ High surge current capabilities
- ⌘ Case style DO- 200AB (E-PUK)

TYPICAL APPLICATIONS

- ⌘ Converters
- ⌘ High power drives
- ⌘ Power supplies
- ⌘ Traction Application

MAJOR RATINGS & CHARACTERISTICS

Parameters	R920 E	Units	
$I_{F(AV)}$	920	A	
@ T_{hs}	55	°C	
$I_{F(RMS)}$	1444	A	
@ T_{hs}	55	°C	
I_{FSM}	@ 50 Hz	5600	A
I^2t	@ 50 Hz	157	KA ² s
V_{RRM} range	2600 TO 3400	V	
T_J	-40 TO 160	°C	



STANDARD RECOVERY DIODES

R920 E

ELECTRICAL SPECIFICATION

VOLTAGE RATINGS

Type Number	Voltage Code	V_{RRM} , max. repetitive peak reverse voltage V	V_{RRM} , max. non-repetitive peak reverse voltage V	I_{DRM} max. @ $T_J = T_J$ max. mA
R920 E	26	2600	2700	50
	28	2800	2900	
	30	3000	3100	
	32	3200	3300	
	34	3400	3500	

FORWARD CONDUCTION

	Parameter	R920E	Units	Conditions
$I_{F(AV)}$	Max. average Forward current @ heat sink temperature	920	A	180° conduction, half sine wave double side cooled
		55	°C	
$I_{F(RMS)}$	Max. RMS Forward current	1444	A	@55°C heat sink temperature (double side cooled)
I_{FSM}	Max. peak one cycle Forward non-repetitive surge current	5600	A	t = 10ms Sinusoidal half wave, Initial $T_J = T_J$ max.
I^2t	Maximum I^2t for fusing	157	kA ² s	
$V_{F(TO)}$	Threshold voltage	0.70	V	$T_J = T_J$ max.
r_f	Forward slope resistance	0.70	mΩ	
V_{FM}	Max. Forward voltage drop	1.38	V	$I_{pk} = 1000A$, $T_J = T_J$ max., $t_p = 10ms$ sine pulse

THERMAL AND MECHANICAL SPECIFICATION

	Parameter	R920E	Units	Conditions
T_J	Max. operating temperature range	-40 TO 160	°C	
T_{stg}	Max. storage temperature range	-40 TO 160		
R_{thJ-hs}	Max. thermal resistance, junction to heat sink	0.05	°C/W	DC operation double side cooled
F	Mounting force, ±10%	9800 (1000)	N (kg)	
w t	Approximate weight	85	g	
	Case style	E-PUK		See outline

SILICON RECTIFIERS

R920E

